NIKO-SEM

Dual N-Channel Enhancement Mode Field Effect Transistor

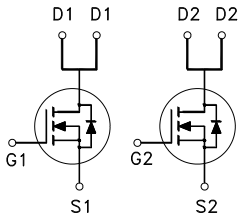
PV6D2DA

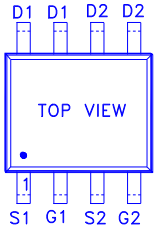
SOP-8

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	25mΩ	6.4A





G : GATE
D : DRAIN
S : SOURCE

100% UIS Tested
100% Rg Tested

Features

- Pb−Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.

ABSOLUTE MAXIMUM RATINGS (T_A = 25 ° C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 ° C	I_D	6.4	A
	T_A = 70 ° C		5.1	
Pulsed Drain Current[1]		I_{DM}	30	
Avalanche Current		I_{AS}	14	
Avalanche Energy	L = 0.1mH	E_{AS}	9.8	mJ
Power Dissipation[3]	T_A = 25 ° C	P_D	2.1	W
	T_A = 70 ° C		1.3	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	° C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	t ≦10s	$R_{\theta JA}$		60	° C / W
Junction-to-Ambient	Steady-State	$R_{\theta JA}$		88	
Junction-to-Case		$R_{\theta JC}$		40	

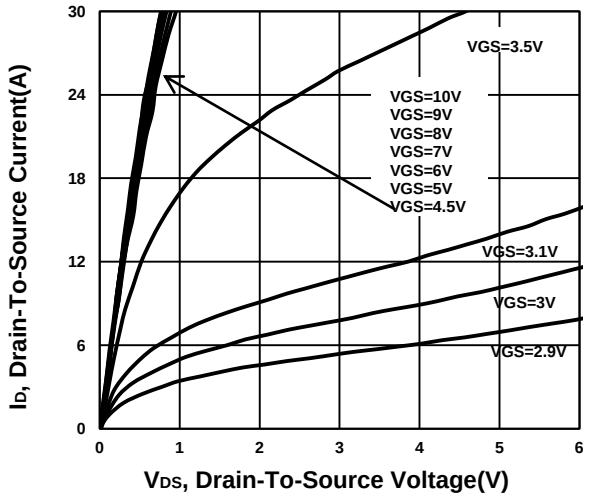
[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C.
[3]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value

ELECTRICAL CHARACTERISTICS (T_J = 25 ° C, Unless Otherwise Noted)

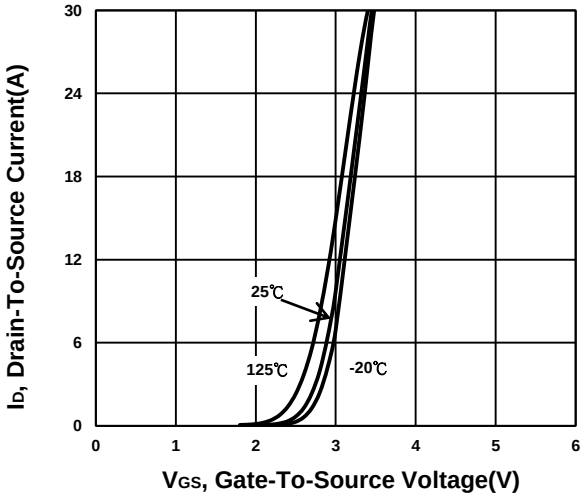
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.79	2.3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V			1	μA
		V_{DS} = 40V, V_{GS} = 0V, T_J = 55 ° C			10	μA
Drain-Source On-State Resistance[4]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 6.4A		23	35	mΩ
		V_{GS} =10V, I_D = 6.4A		19.5	25	mΩ
Forward Transconductance[4]	g_{fs}	V_{DS} = 5V, I_D = 6.4A		25		S
DYNAMIC[5,6]						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz		435		pF
Output Capacitance	C_{oss}			62		pF
Reverse Transfer Capacitance	C_{rss}			39		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		4.2		Ω
Total Gate Charge	$Q_{g(VGS=10V)}$	V_{DS} = 20V , I_D = 6.4A	7.6	9.5	11.4	nC
	$Q_{g(VGS=4.5V)}$		4.2	5.2	6.2	nC
Gate-Source Charge	Q_{gs}		1	1.3	1.6	nC
Gate-Drain Charge	Q_{gd}		1.8	3	4.2	nC
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = 20V , I_D ≅ 6.4A, V_{GS} = 10V, R_{GEN} =6Ω		6		nS
Rise Time	t_r			79		nS
Turn-Off Delay Time	$t_{d(off)}$			23		nS
Fall Time	t_f			101		nS
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 ° C)						
Continuous Current	I_S				1.6	A
Forward Voltage[4]	V_{SD}	I_F = 6.4A, V_{GS} = 0V			1.3	V
Diode Reverse Recovery Time	t_{rr}	I_F= 6.4A, dI/dt=100A/μs		5.1		nS
Diode Reverse Recovery Charge	Q_{rr}			1.6		nC

[4]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[5]Independent of operating temperature.
[6]Guaranteed by design, not subject to production testing.

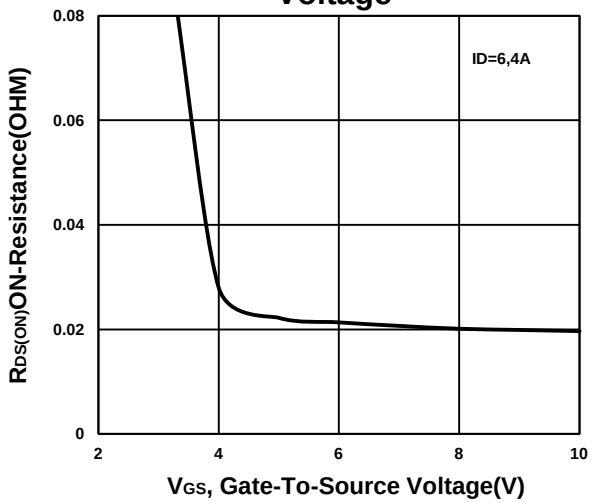
Output Characteristics



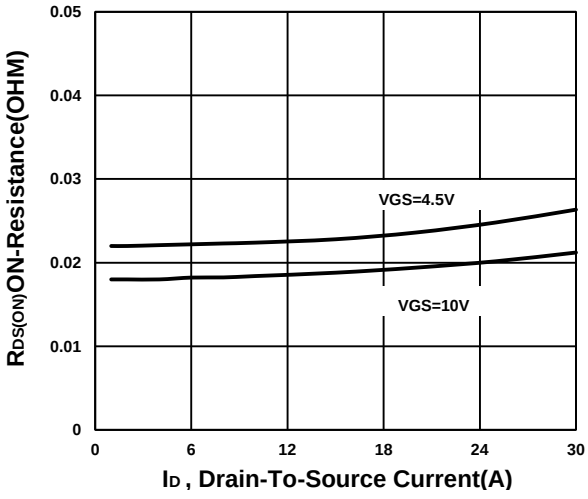
Transfer Characteristics



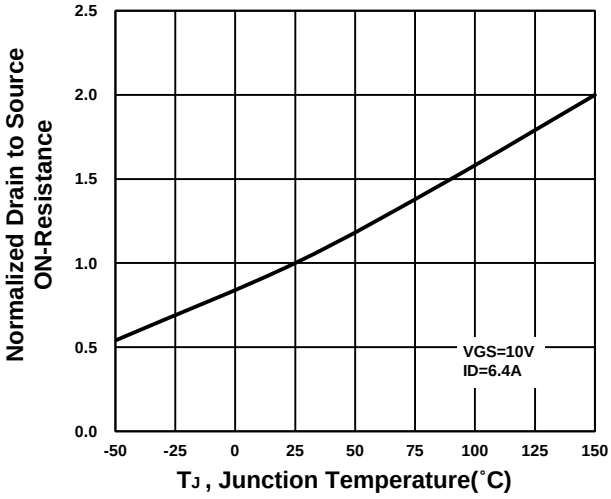
On-Resistance VS Gate-To-Source Voltage



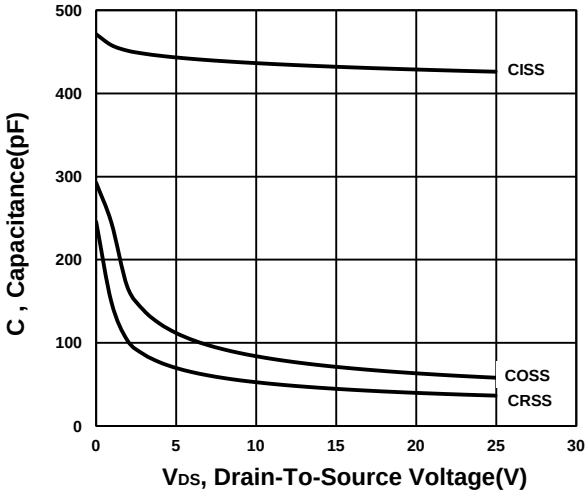
On-Resistance VS Drain Current



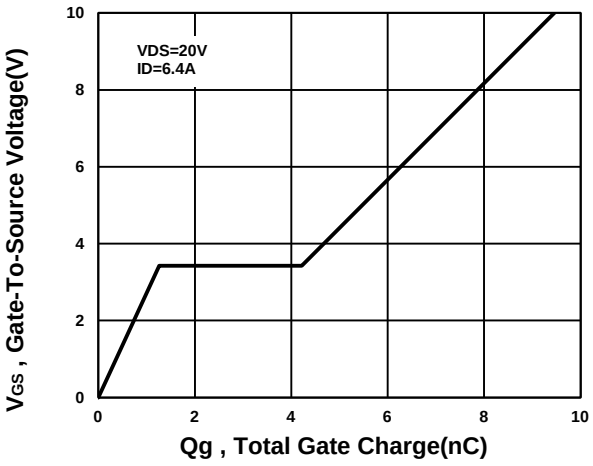
On-Resistance VS Temperature



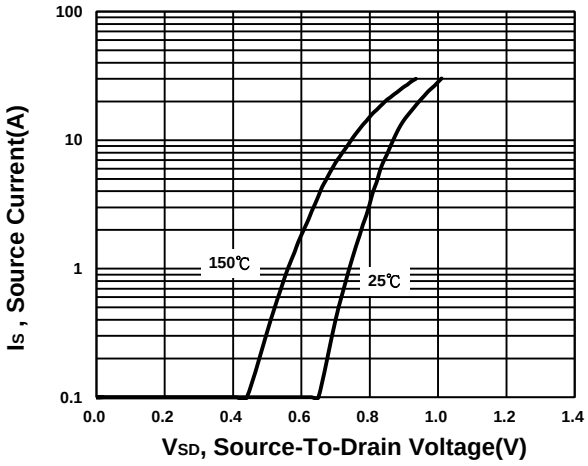
Capacitance Characteristic



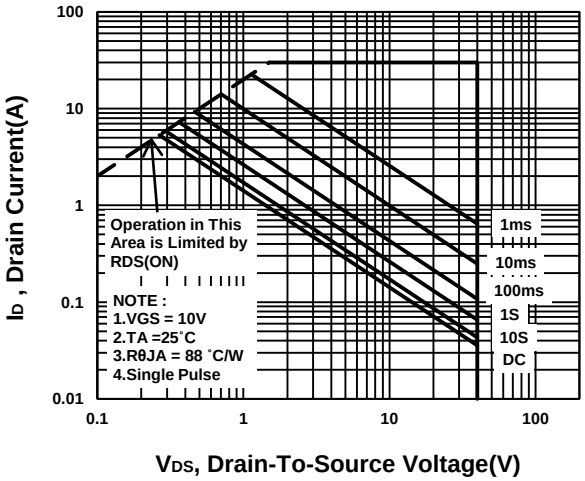
Gate charge Characteristics



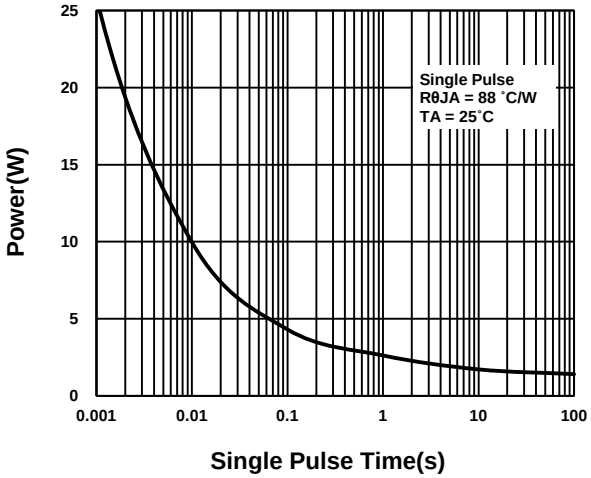
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve